



# STB15NM60ND - STF/15NM60ND STP15NM60ND - STW15NM60ND

N-channel 600 V - 0.27  $\Omega$  - 14 A - FDmesh™ II Power MOSFET  
D<sup>2</sup>PAK, I<sup>2</sup>PAK, TO-220, TO-220FP, TO-247

## Features

Type	V <sub>DSS</sub> (@T <sub>jmax</sub> )	R <sub>DS(on)</sub> max	I <sub>D</sub>
STB15NM60ND	650 V	0.299 $\Omega$	14 A
STF15NM60ND			14 A
STI15NM60ND			14 A <sup>(1)</sup>
STP15NM60ND			14 A
STW15NM60ND			14 A

1. Limited only by maximum temperature allowed

- The worldwide best R<sub>DS(on)</sub>\* area amongst the fast recovery diode devices
- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance
- Extremely high dv/dt and avalanche capabilities

## Application

- Switching applications

## Description

The FDmesh™ II series belongs to the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a new vertical structure to the company's strip layout and associates all advantages of reduced on-resistance and fast switching with an intrinsic fast-recovery body diode. Strongly recommended for bridge topologies, in ZVS phase-shift converters.

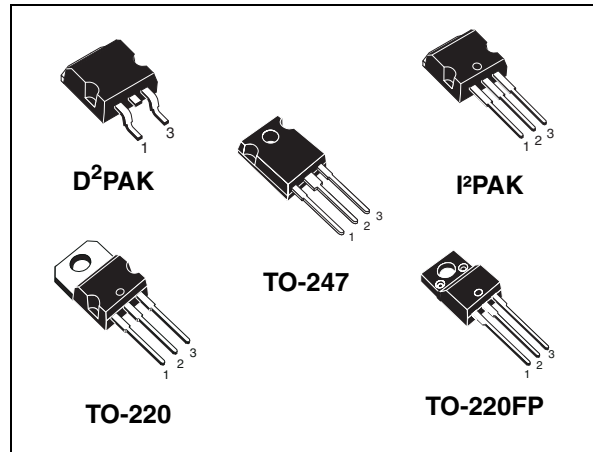


Figure 1. Internal schematic diagram

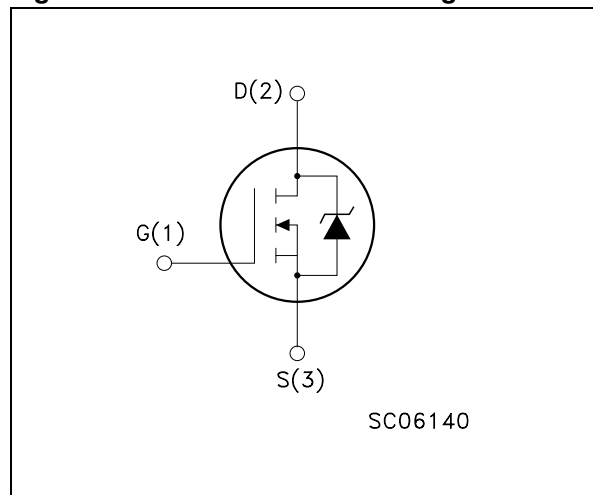


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB15NM60ND	15NM60ND	D <sup>2</sup> PAK	Tape and reel
STF15NM60ND	15NM60ND	TO-220FP	Tube
STI15NM60ND	15NM60ND	I <sup>2</sup> PAK	Tube
STP15NM60ND	15NM60ND	TO-220	Tube
STW15NM60ND	15NM60ND	TO-247	Tube

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		DPAK/I <sup>2</sup> PAK TO-220/IPAK	TO-220FP	
V <sub>DS</sub>	Drain-source voltage (V <sub>GS</sub> =0)	600		V
V <sub>GS</sub>	Gate-source voltage	± 25		V
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25 °C	14	14 <sup>(1)</sup>	A
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 100 °C	9	9 <sup>(1)</sup>	A
I <sub>DM</sub> <sup>(2)</sup>	Drain current (pulsed)	56	56 <sup>(1)</sup>	A
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25 °C	125	30	W
dv/dt <sup>(3)</sup>	Peak diode recovery voltage slope	40		V/ns
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; T <sub>C</sub> =25 °C)	--	2500	V
T <sub>stg</sub>	Storage temperature	-55 to 150		°C
T <sub>j</sub>	Operating junction temperature	150		°C

1. Limited only by maximum temperature allowed
2. Pulse width limited by safe operating area
3. I<sub>SD</sub> ≤ 14 A, di/dt ≤ 400 A/μs, V<sub>DD</sub> = 80% V<sub>(BR)DSS</sub>

**Table 3. Thermal data**

Symbol	Parameter	TO-220	I <sup>2</sup> PAK	TO-247	D <sup>2</sup> PAK	TO-220FP	Unit
R <sub>thj-case</sub>	Thermal resistance junction-case max	1				4.2	°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-amb max	62.5		50	--	62.5	°C/W
R <sub>thj-pcb</sub>	Thermal resistance junction-pcb max	--	--	--	30	--	°C/W
T <sub>l</sub>	Maximum lead temperature for soldering purposes	300					°C

**Table 4. Avalanche characteristics**

Symbol	Parameter	Max value	Unit
$I_{AS}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_j$ max)	6	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ °C}$ , $I_D = I_{AS}$ , $V_{DD} = 50\text{ V}$ )	300	mJ

## 2 Electrical characteristics

( $T_{CASE}=25^{\circ}C$  unless otherwise specified)

**Table 5. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1 \text{ mA}, V_{GS} = 0$	600			V
$dv/dt^{(1)}$	Drain-source voltage slope	$V_{DD} = 480 \text{ V}, I_D = 14 \text{ A}, V_{GS} = 10 \text{ V}$	30			V/ns
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max rating}, V_{DS} = \text{Max rating}, @ 125^{\circ}C$			1 100	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20 \text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10 \text{ V}, I_D = 7 \text{ A}$		0.27	0.299	$\Omega$

1. Value measured at turn off under inductive load

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15 \text{ V}, I_D = 7 \text{ A}$		10		S
$C_{iss}$ $C_{oss}$ $C_{rss}$	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}, V_{GS} = 0$		1250 65 5		pF pF pF
$C_{oss \text{ eq.}}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0, V_{DS} = 0 \text{ V to } 480 \text{ V}$		180		pF
$R_g$	Gate input resistance	$f = 1 \text{ MHz}$ Gate DC Bias=0 Test signal level=20 mV open drain		4		$\Omega$
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 480 \text{ V}, I_D = 14 \text{ A}$ $V_{GS} = 10 \text{ V}$ (see Figure 19)		40 8 22		nC nC nC

1. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

2.  $C_{oss \text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

**Table 7.      Switching times**

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$ , $I_D = 7\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ <i>(see Figure 18)</i>		17		ns
$t_r$	Rise time			20		ns
$t_{d(off)}$	Turn-off delay time			47		ns
$t_f$	Fall time			28		ns

**Table 8.      Source drain diode**

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$I_{SD}$	Source-drain current				14	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				56	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 14\text{ A}$ , $V_{GS} = 0$			1.3	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 14\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 100\text{ V}$ <i>(see Figure 20)</i>		148		ns
$Q_{rr}$	Reverse recovery charge			910		nC
$I_{RRM}$	Reverse recovery current			12		A
$t_{rr}$	Reverse recovery time	$V_{DD} = 100\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$ , $I_{SD} = 14\text{ A}$ $T_j = 150\text{ }^\circ\text{C}$ <i>(see Figure 20)</i>		190		ns
$Q_{rr}$	Reverse recovery charge			1280		nC
$I_{RRM}$	Reverse recovery current			13		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220 / D<sup>2</sup>PAK / I<sup>2</sup>PAK

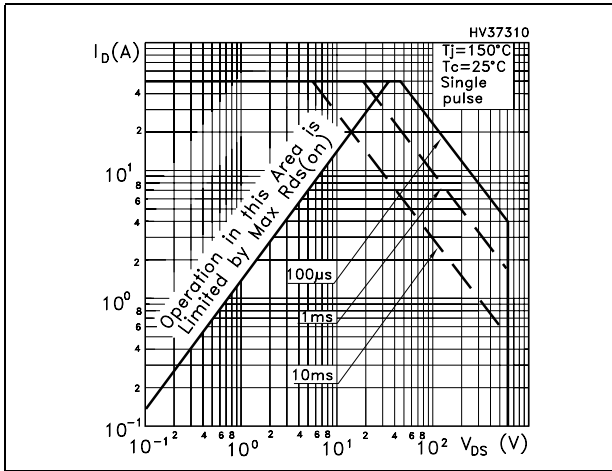


Figure 3. Thermal impedance for TO-220 / D<sup>2</sup>PAK / I<sup>2</sup>PAK

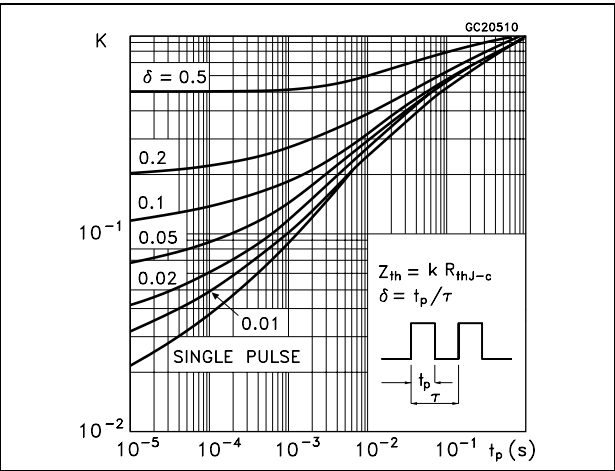


Figure 4. Safe operating area for TO-220FP

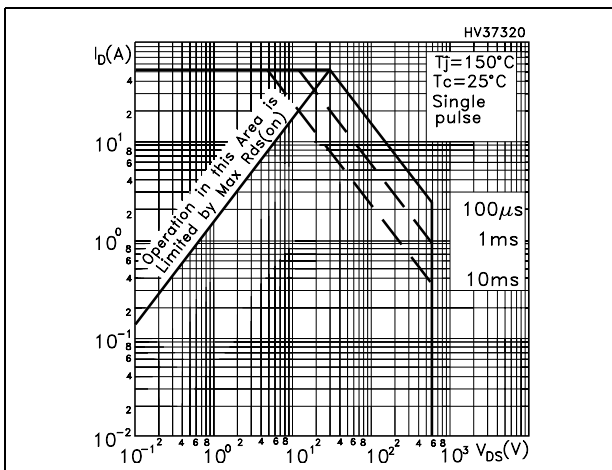


Figure 5. Thermal impedance for TO-220FP

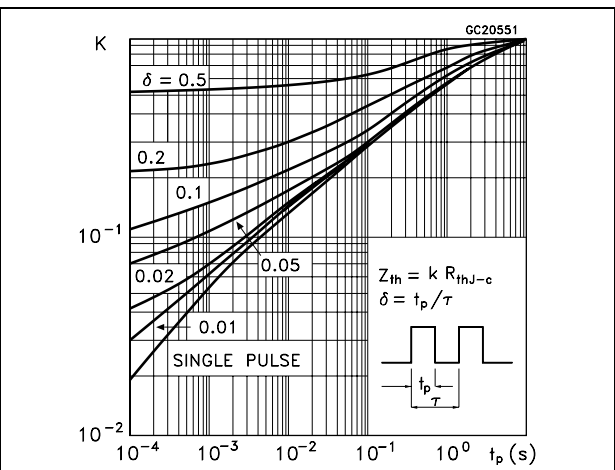


Figure 6. Safe operating area for TO-247

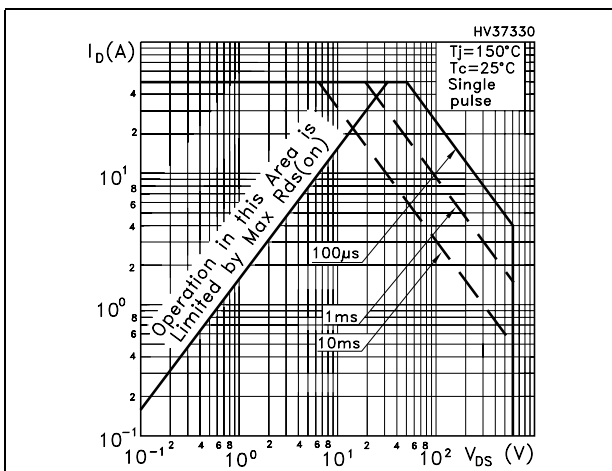


Figure 7. Thermal impedance for TO-247

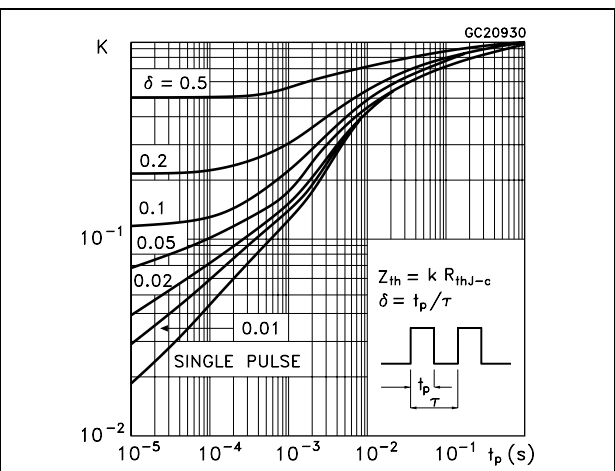


Figure 8. Output characteristics

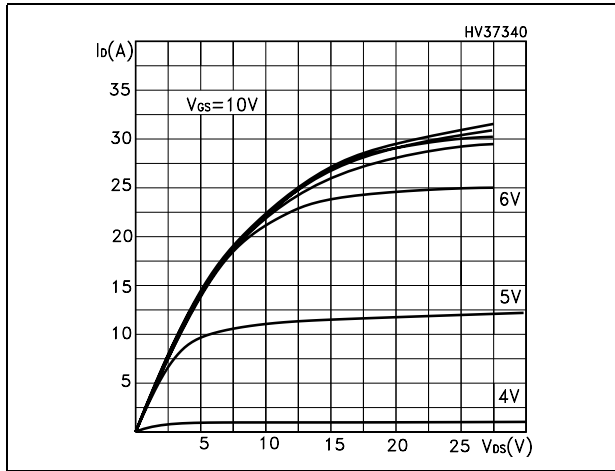


Figure 9. Transfer characteristics

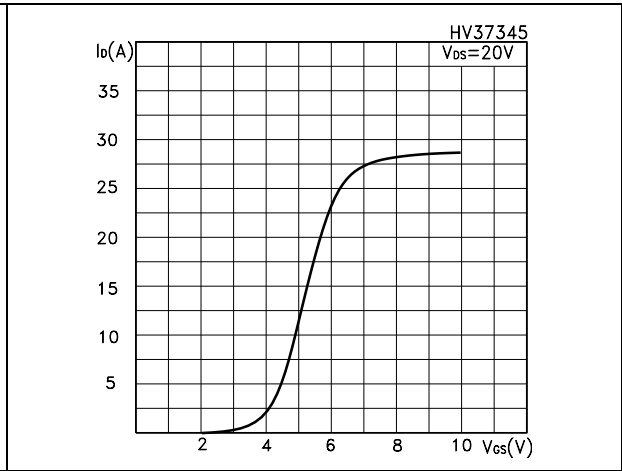


Figure 10. Transconductance

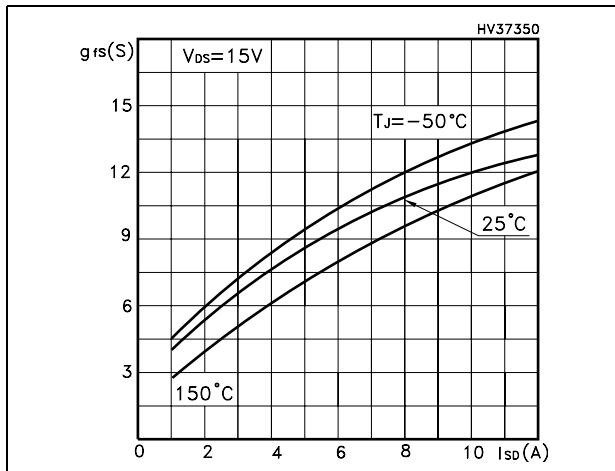


Figure 11. Static drain-source on resistance

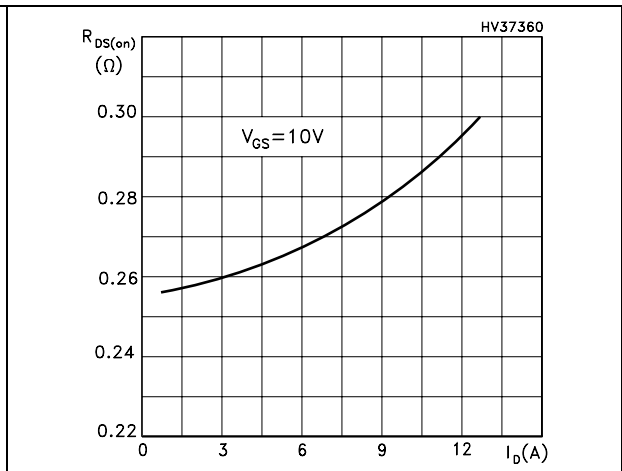


Figure 12. Gate charge vs gate-source voltage

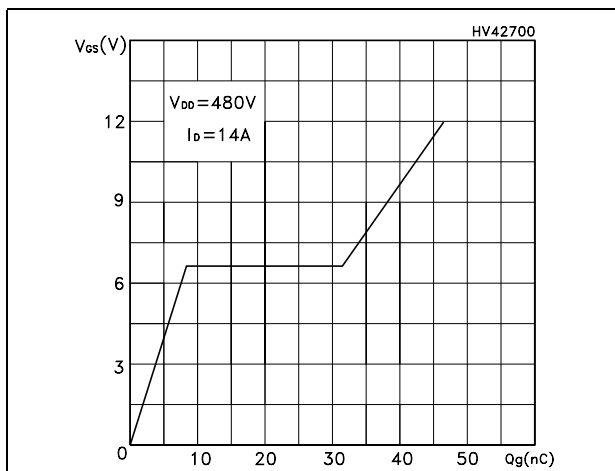


Figure 13. Capacitance variations

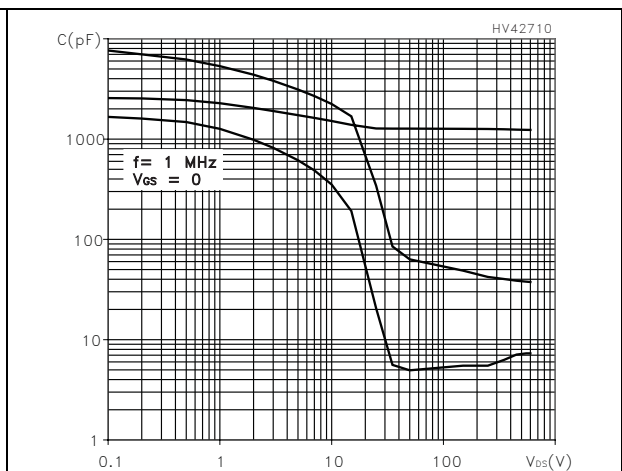




Figure 14. Normalized gate threshold voltage vs temperature

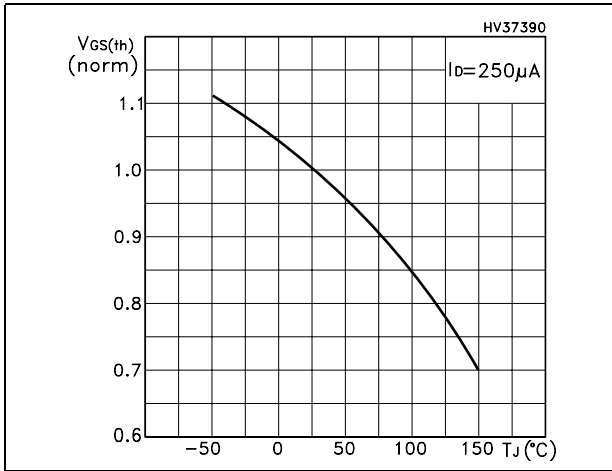


Figure 15. Normalized on resistance vs temperature

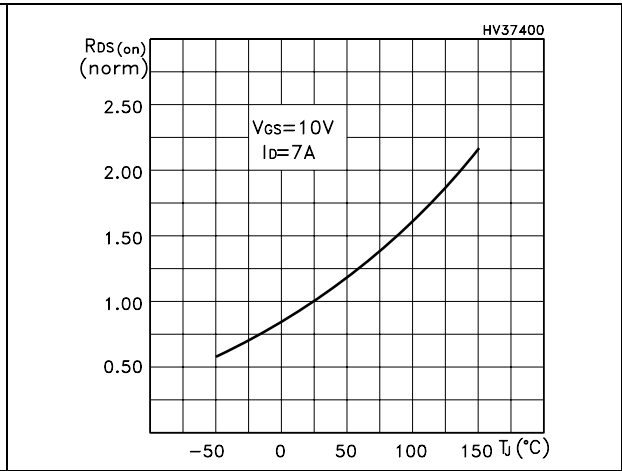


Figure 16. Source-drain diode forward characteristics

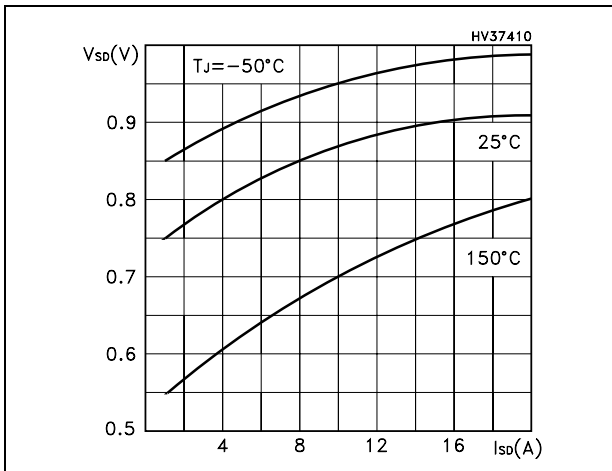
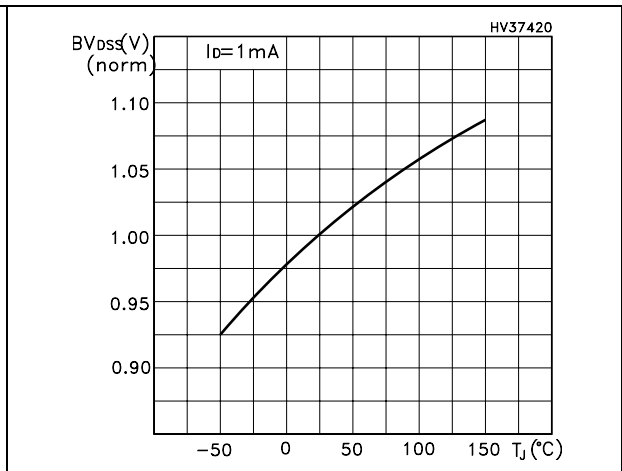


Figure 17. Normalized  $B_{VDSS}$  vs temperature



### 3 Test circuit

Figure 18. Switching times test circuit for resistive load

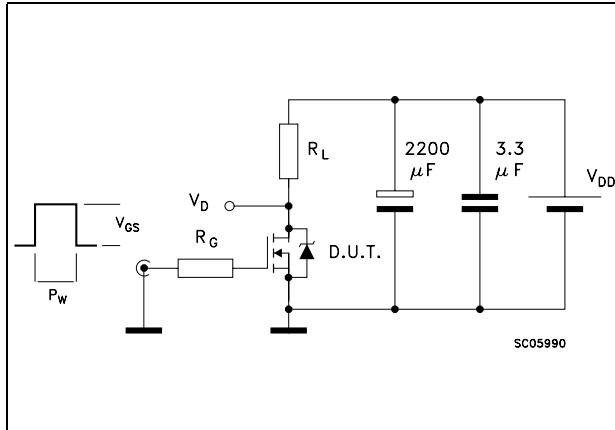


Figure 19. Gate charge test circuit

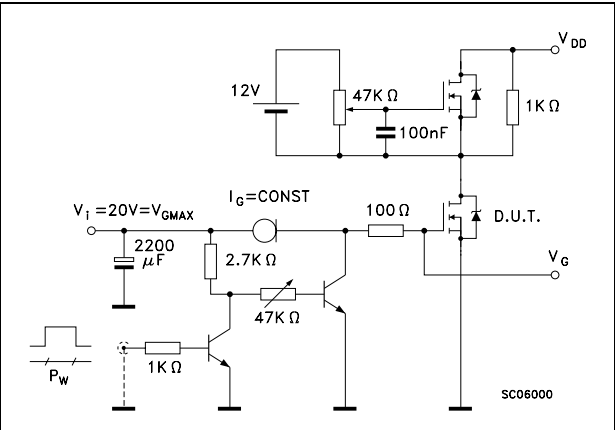


Figure 20. Test circuit for inductive load switching and diode recovery times

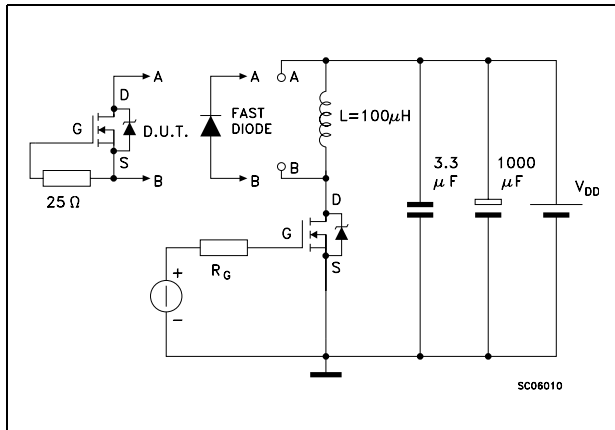


Figure 21. Unclamped Inductive load test circuit

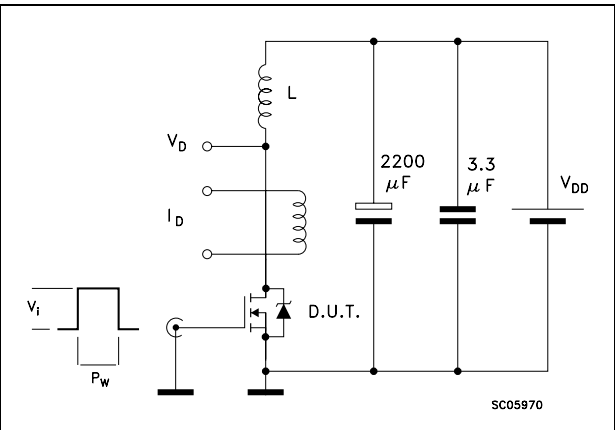


Figure 22. Unclamped inductive waveform

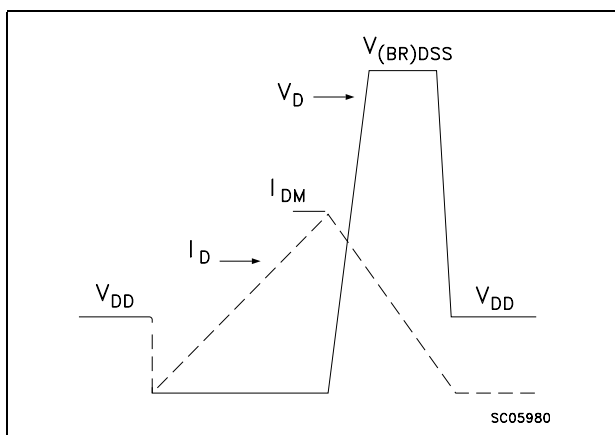
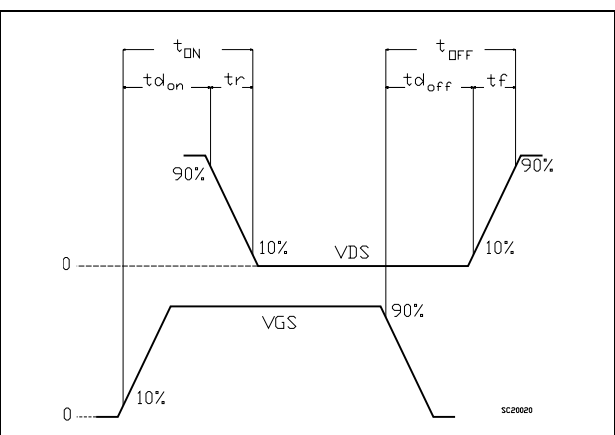


Figure 23. Switching time waveform

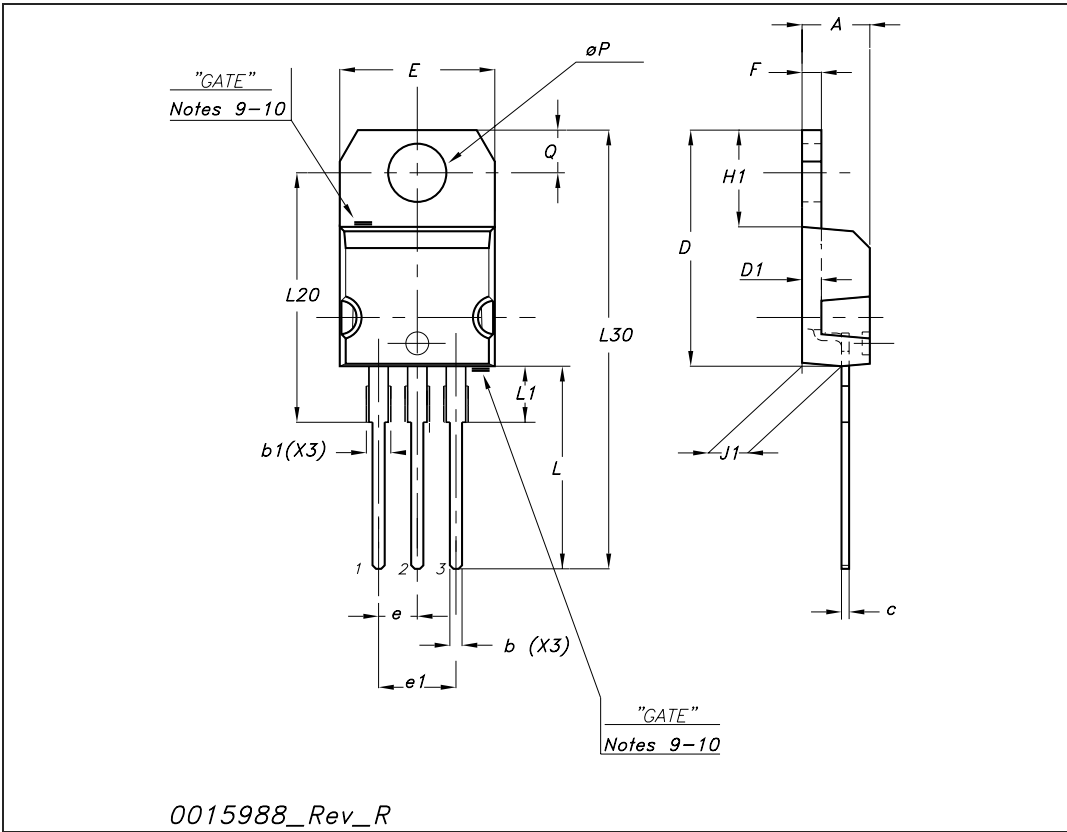


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

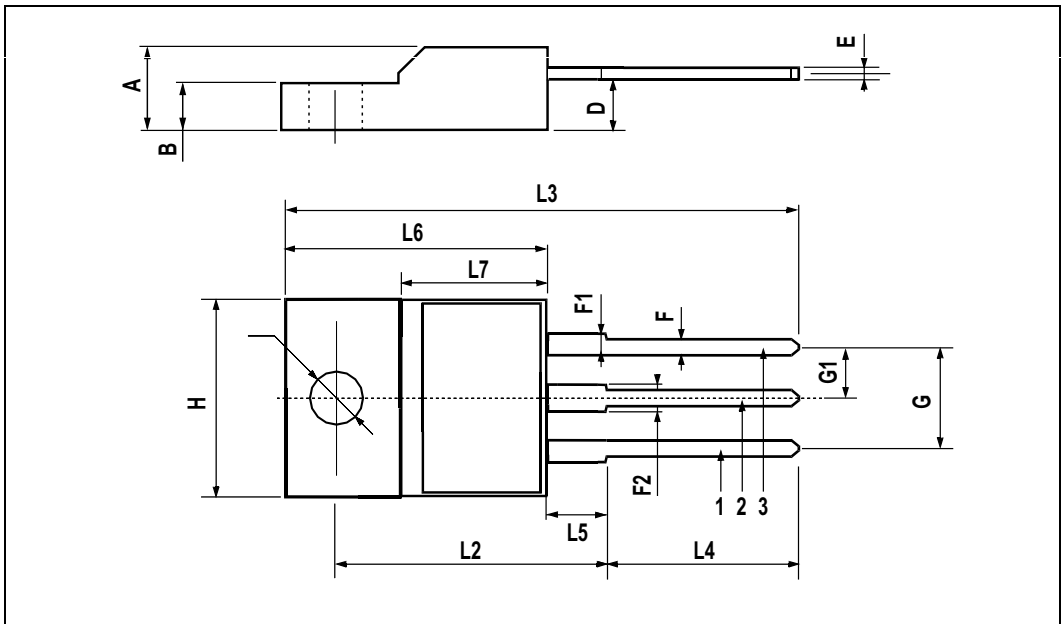
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
∅P	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



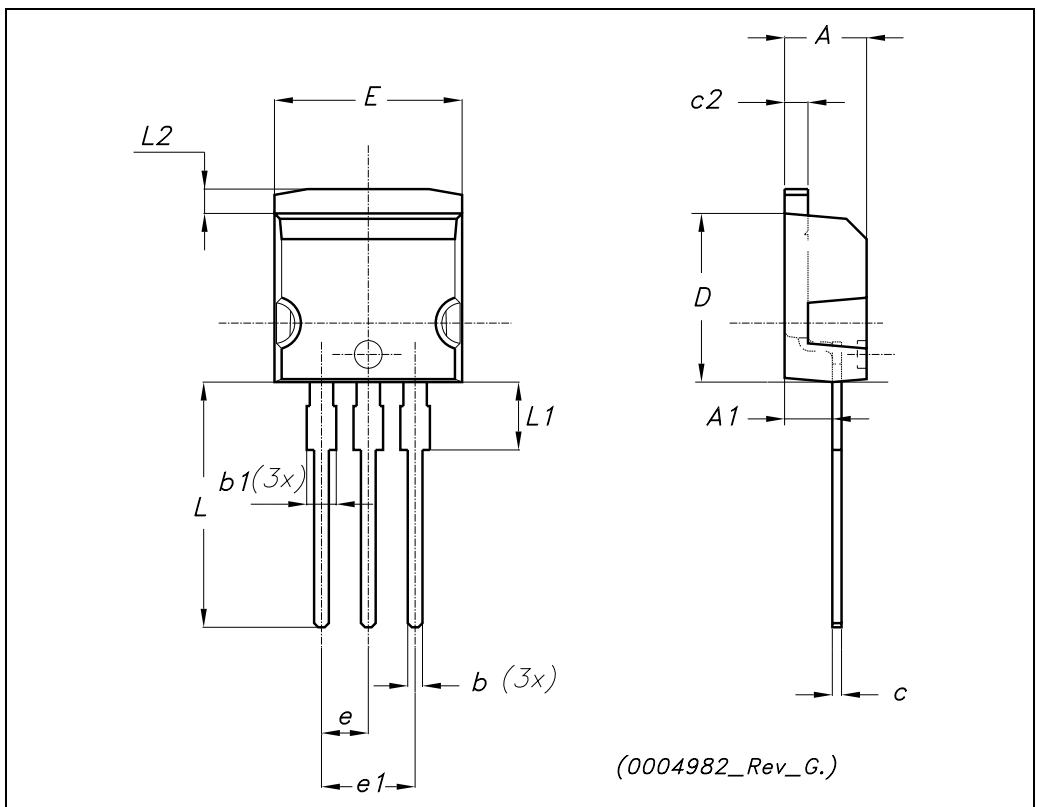
**TO-220FP MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



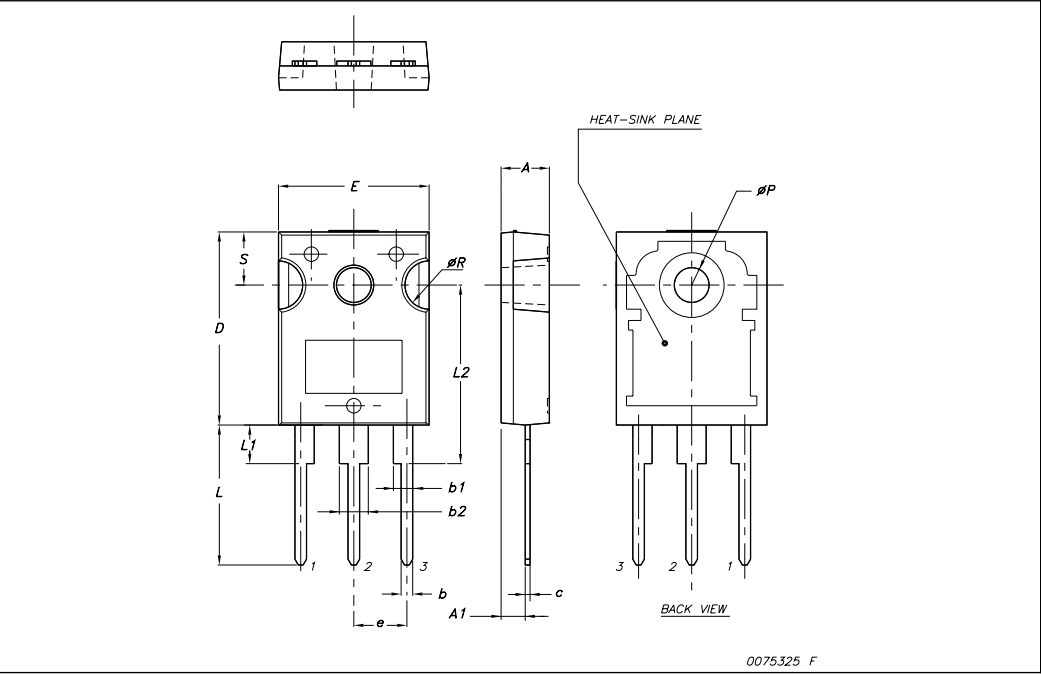
**TO-262 (I<sup>2</sup>PAK) MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



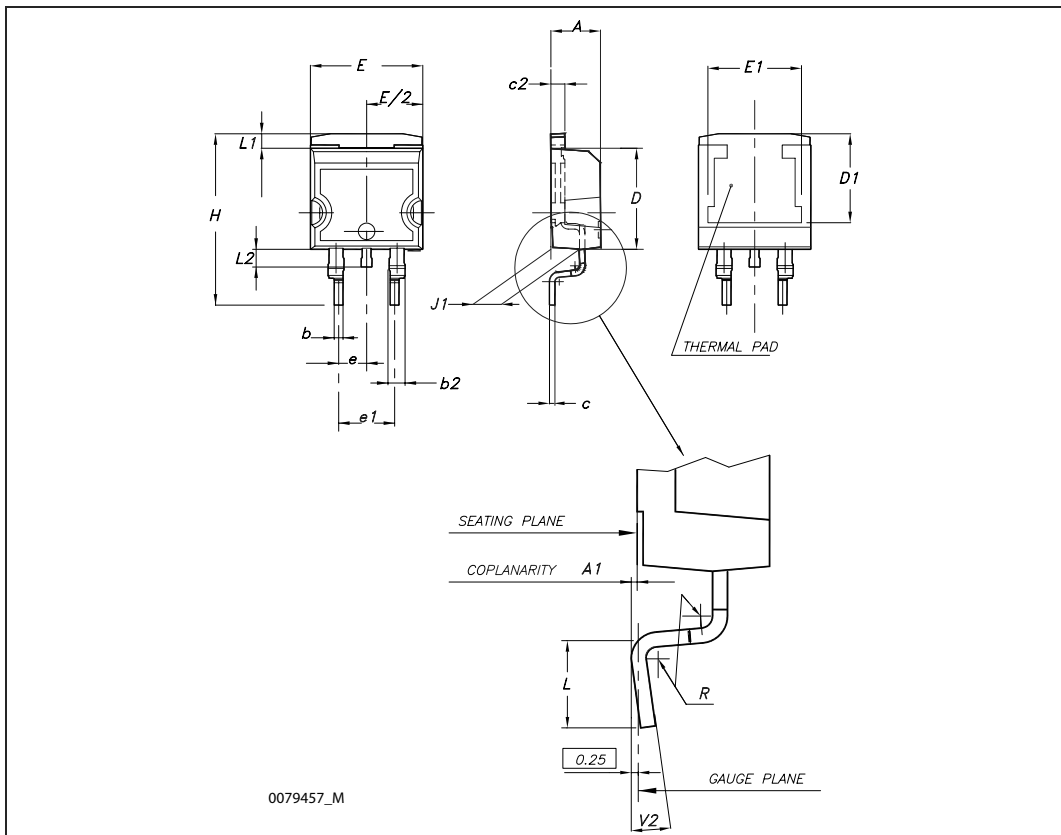
**TO-247 Mechanical data**

Dim.	mm.		
	Min.	Typ	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øP	3.55		3.65
øR	4.50		5.50
S		5.50	



**D<sup>2</sup>PAK (TO-263) mechanical data**

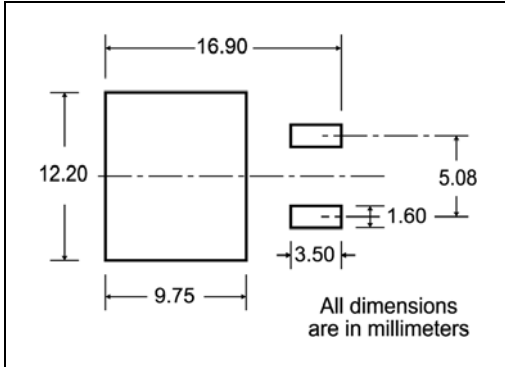
Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°





## 5 Packaging mechanical data

### D<sup>2</sup>PAK FOOTPRINT



### TAPE AND REEL SHIPMENT

40 mm min. Access hole at slot location

Full radius

2.5mm min. width

Tape slot in core for tape start

#### REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

#### TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

10 pitches cumulative tolerance on tape +/- 0.2 mm

Center line of cavity

User Direction of Feed

TRL

FEED DIRECTION

Bending radius R min.

\* on sales type

## 6 Revision history

**Table 9. Document revision history**

Date	Revision	Changes
06-Mar-2008	1	First release
24-Apr-2008	2	$V_{GS}$ value on <a href="#">Table 2</a> changed.

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